

LIST OF CONTRIBUTIONS TO NATIONAL AND INTERNATIONAL CONGRESSES 2019

1. Doblas, A.; Carulla, M.; Flores, D.; Hidalgo, S.; Pellegrini, G.; Quirion, D.
Low Gain Avalanche Detector (LGAD) for Synchrotron and HEP Experiments
6th EIROForum School on instrumentation, Noordwijk (The Netherlands), International
2. Hoffmann, V. Soler, A. Mihaila, N. Kaminski
Power Cycling Test on 3.3 kV SiC MOSFETs and the Effects of Bipolar Degradation on the Temperature Estimation by VSD-Method.
Proceeding of IEEE 31st International Symposium on Power Semiconductor Devices and ICs (ISPSD), 2019 International
3. P. Godignon,
SiC power devices and their processing
EMRS Spring meeting, May 27-31, 2019, Nice (France), International
4. P. Godignon
State of the art of 4H-SiC MOSFET processing
Workshop WinSiC4AP, March 6-7, 2019, Tours (France), International
5. X. Jordà, X. Perpiñà, M. Vellvehi, P. Godignon, R. Seddon, J. Maudes, I. Obieta.
Analysis of materials suitable for diamond-based power devices packaging.
Workshop on Advances in Packaging and Components (APAC 2019), Noordwijk (Netherlands), 14-15 March 2019
6. L.A. Navarro, X. Perpiñà, M. Vellvehi, O. Aviñó and X. Jordà.
Electrical Behaviour of Ag Sintered Die-attach Layer after Thermal Cycling in High Temperature Power Electronics Application.
XXVI Congreso Internacional Anual de la Sociedad Mexicana de Ingeniería Mecánica (SOMIM 2019), Universidad Michoacana de San Nicolás Hidalgo (México), pp. 23 – 26, 2019; International
7. V. Banu, M. Popescu and P. Godignon.
Latest Concept to Generate Temperature Compensated Voltage Reference.
2019 International Semiconductor Conference (CAS), Sinaia, Romania; pp. 129-132; 2019; International
8. V. Banu, M. Popescu and P. Godignon.
Delta Reference, the Latest High Temperature Compensated Voltage Reference Concept.
2019 European Space Power Conference (ESPC), Juan-les-Pins, France, 2019, pp. 1-8, International

9. B. Asllani, A. Castellazzi, O. Aviñó-Salvadó, A. Fayyaz, H. Morel, D. Planson.
Vth-Hysteresis and Interface States Characterisation in SiC Power MOSFETs with Planar and Trench Gate.
International Reliability Physics Symposium (IRPS) 2019, Monterey, CA, USA, April 2019; International.

10. Guimerà-Brunet, A., Masvidal-Codina, E., Illa, X., Dasilva, M., Bonaccini-Calia, A., Prats-Alfonso, E., Martínez-Aguilar, J., De la Cruz, J.M., Garcia-Cortadella, R., Schaefer, N., Barbero, A., Godignon, P., Rius, G., Del Corro, E., Bousquet, J., Hébert, C., Wykes, R., Sanchez-Vives, M.V., Villa, R., Garrido, J.A.
Neural interfaces based on flexible graphene transistors: A new tool for electrophysiology
IEEE International Electron Devices Meeting (IEDM), San Francisco, CA, USA, December 2019; International